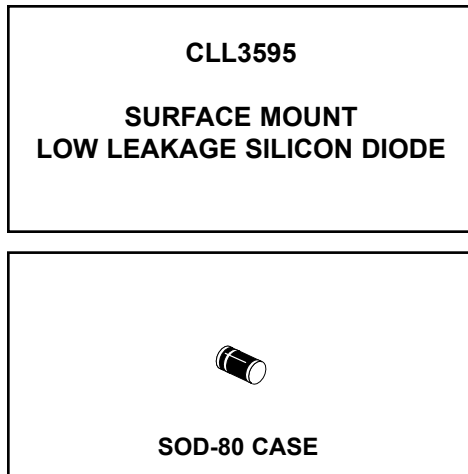




DESCRIPTION:

The CENTRAL SEMICONDUCTOR CLL3595 type is an epitaxial planar silicon diode, manufactured in a hermetically sealed glass surface mount package, designed for low leakage, high conductance applications.

MAXIMUM RATINGS: (T_A=25°C)

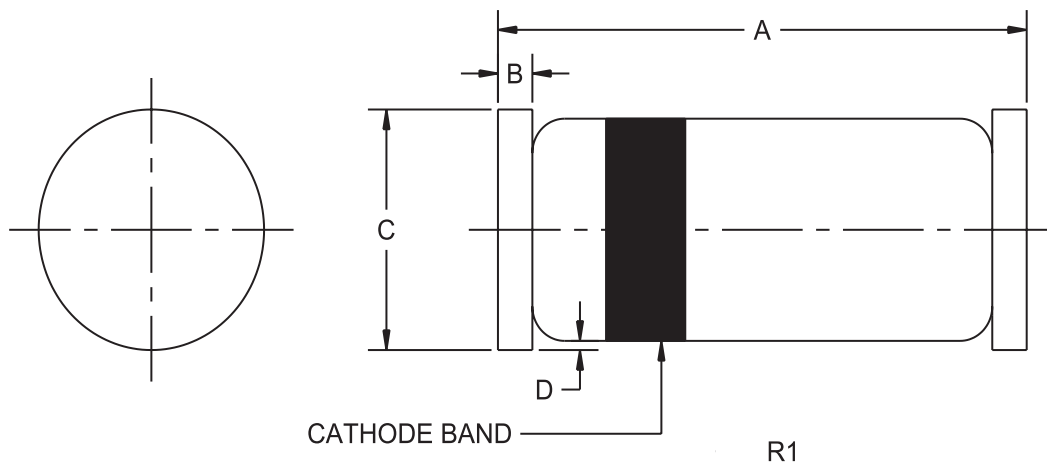
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	150	V
Peak Working Reverse Voltage	V _{RWM}	125	V
Average Forward Current	I _O	150	mA
Forward Steady-State Current	I _F	225	mA
Recurrent Peak Forward Current	i _f	600	mA
Peak Forward Surge Current (1.0s pulse)	I _{FSM}	500	mA
Peak Forward Surge Current (1.0μs pulse)	I _{FSM}	4.0	A
Power Dissipation	P _D	500	mW
Operating and Storage			
Junction Temperature	T _J ,T _{stg}	-65 to +200	°C
Thermal Resistance	Θ _{JA}	350	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
BV _R	I _R =100μA	150		V
I _R	V _R =125V		1.0	nA
I _R	V _R =125V, T _A =125°C		500	nA
I _R	V _R =125V, T _A =150°C		3.0	μA
I _R	V _R =30V, T _A =125°C		300	nA
V _F	I _F =1.0mA	0.54	0.69	V
V _F	I _F =5.0mA	0.62	0.77	V
V _F	I _F =10mA	0.65	0.80	V
V _F	I _F =50mA	0.75	0.88	V
V _F	I _F =100mA	0.79	0.92	V
V _F	I _F =200mA	0.83	1.00	V
C _T	V _R =0, f=1.0MHz		8.0	pF
t _{rr}	V _R =3.5V, I _f =10mA, R _L =1.0kΩ		3.0	μs

**SURFACE MOUNT
LOW LEAKAGE SILICON DIODE**

SOD-80 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.130	0.146	3.30	3.71
B	0.016		0.41	
C (DIA)	0.051	0.067	1.30	1.70
D	-	0.004	-	0.10

SOD-80 (REV:R1)

R1 (25-September 2001)